

**SEMICONDUCTOR DEVICES HAVING CAPACITORS OF METAL-
INSULATOR-METAL STRUCTURE WITH COEXTENSIVE OXIDATION
BARRIER PATTERN AND LOWER ELECTRODE BOTTOM AND
METHODS OF FORMING THE SAME**

5

Abstract of the Disclosure

A semiconductor device having MIM capacitors is configured so that the
bottom surface of the lower electrode and a top surface area of an oxidation barrier
pattern are substantially equal. Related methods for forming the device are also
10 described.